

## **DETAILED ACTION**

### ***Continued Examination Under 37 CFR 1.114***

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on March 01<sup>st</sup>, 2010 has been entered.
2. The Amendment filed on March 01<sup>st</sup>, 2010 is acknowledged. By this amendment, claims 1 and 7 have been amended, claim 47 is newly added and claims 14-46 have been cancelled. Accordingly, claims 1-16 and 47 are currently pending in this application and claims 1 and 7 are in independent form.

### ***Allowable Subject Matter***

3. Claims 1-16 and 47 are allowed over prior art of record and renumbered as 1-17, respectively.

### ***Reasons For Allowance***

4. The following is an examiner's statement of reasons for allowance:

After further search and consideration of Applicant's response filed on March 01<sup>st</sup>, 2010 (see Applicant's arguments in Page 9, line 1 to Page 10, line 10 of the March 01<sup>st</sup>, response), it is determined that the prior art of record neither anticipates nor renders obvious the claimed subject matter of the instant application as a whole taken alone or in combination.

5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

### ***Conclusion***

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
  - Wu et al. (U.S. Patent 7,235,482) disclose an atomic layer deposition method is used to deposit a TiN or TiSiN film having a thickness of about 50 nm or less on a substrate.
  - Hayashi et al. (U.S. Patent 6,156,107) disclose a trap apparatus includes a case provided for a gas exhaust system used for a film forming equipment which carries out a film forming process on an object, a gas supply port, made in the case and connected to an exhaust pipe of the gas exhaust system, for introducing an exhaust gas flowing through the exhaust pipe, into the case.

### ***Correspondence***

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to KHIEM D. NGUYEN whose telephone number is (571)272-1865. The examiner can normally be reached on Monday-Friday (8:30 AM - 5:30 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Khiem D. Nguyen/  
Primary Examiner, Art Unit 2823  
April 09<sup>th</sup>, 2010